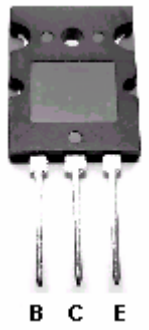
Silicon PNP Power Transistors 2SA1302

DESCRIPTION

・With TO-3PL package
・Complement to type 2SC3281

APPLICATIONS

・Power amplifier applications
・Recommended for 100W high fidelity audio frequency amplifier output stage



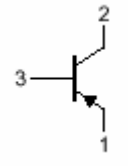


Fig.1 simplified outline (TO-3PL) and symbol

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-200	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-1.5	A
P_C	Collector power dissipation	T_C=25℃	150	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA ;I_B=0	-200			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-8A; I_B=-0.8A			-2.5	V
V_{BE}	Base-emitter voltage	I_C=-8A ; V_{CE}=-5V			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-200V; I_E=0			-5	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-5	μA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-5V	55		160	
h_{FE-2}	DC current gain	I_C=-8A ; V_{CE}=-5V	35			
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		25		MHz
C_{OB}	Collector output capacitance	I_E=0;f=1MHz;V_{CB}=-10V		470		pF

◆ **h_{FE-1} classifications**

R	O
55-110	80-160

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PACKAGE OUTLINE

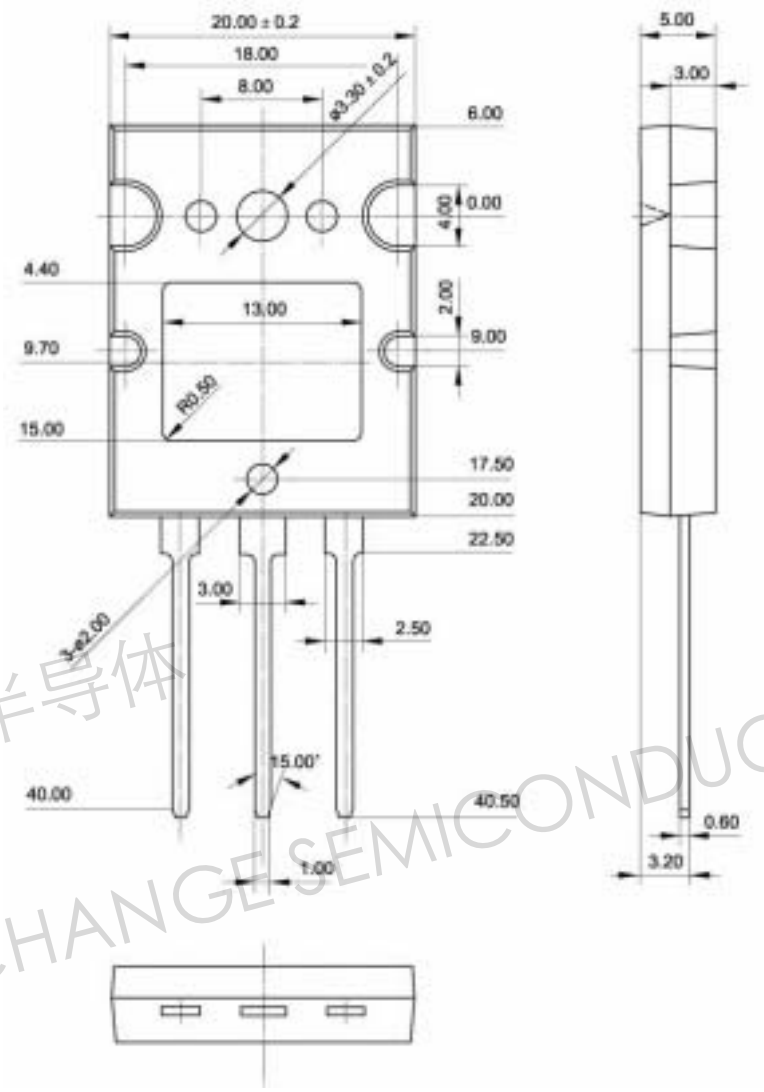

Fig.2 Outline dimensions (unindicated tolerance:±0.50 mm)

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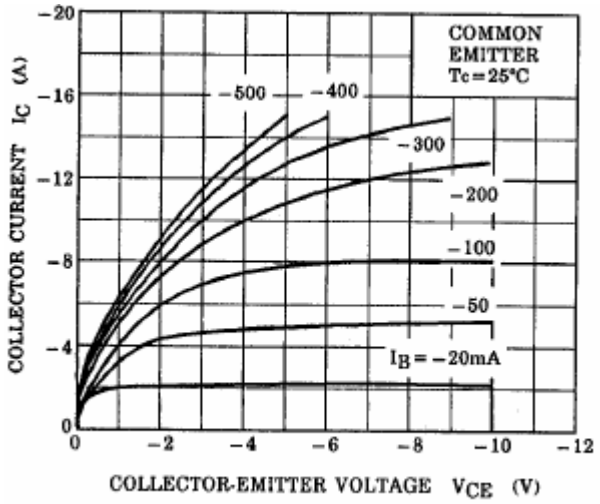

Fig.3 Static Characteristic

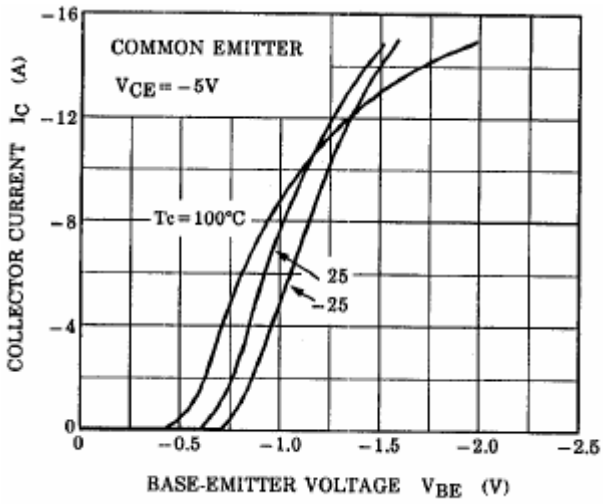

Fig.3 Base-Emitter On Voltage

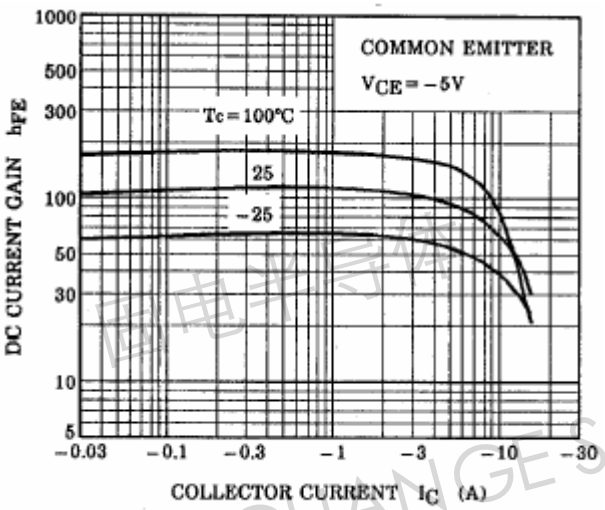

Fig.5 DC current Gain

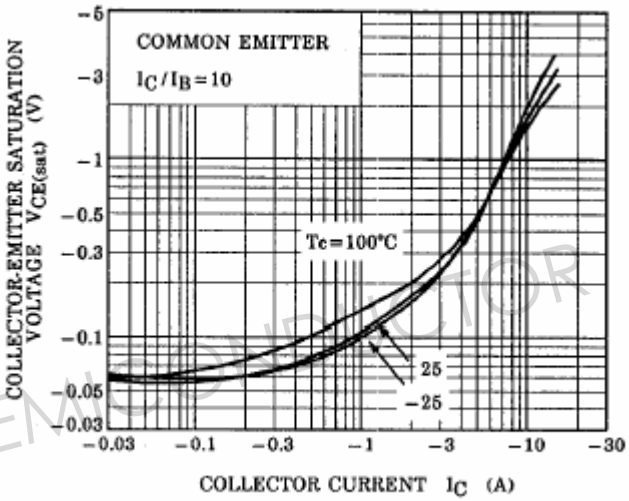

Fig.6 Collector-Emitter Saturation Voltage

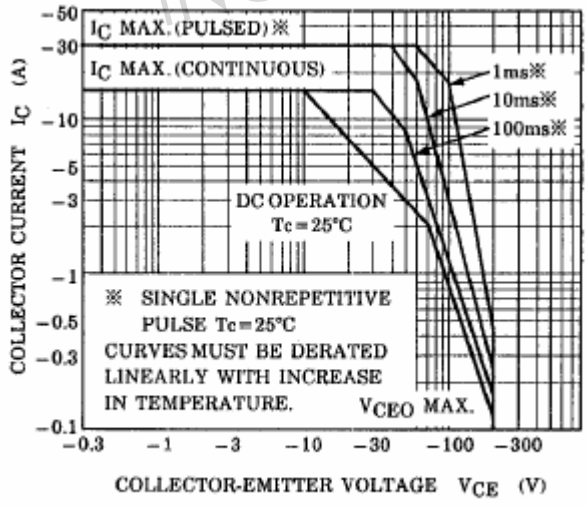

Fig.7 Safe Operating Area